



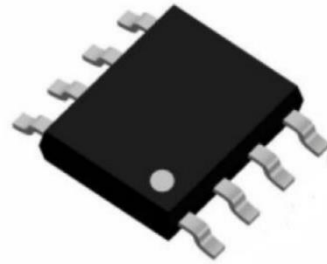
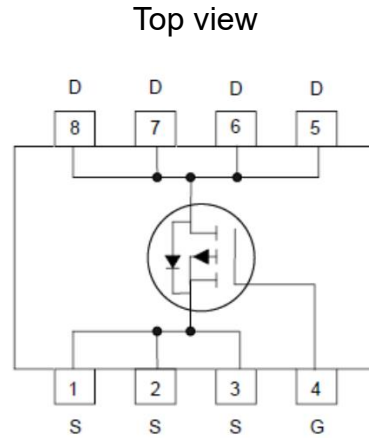
# SSC8239GS1

## P-Channel Enhancement Mode MOSFET

### ➤ Features

VDS	VGS	RDSON Typ.	ID
-35V	±20V	6mR@-10V	-68A
		8mR@-4V5	

### ➤ Pin configuration



Bottom View

### ➤ Description

This device is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device is particularly suited for low voltage power management requiring a wide range of given voltage ratings(4.5V~25V) such as load switch and battery protection.

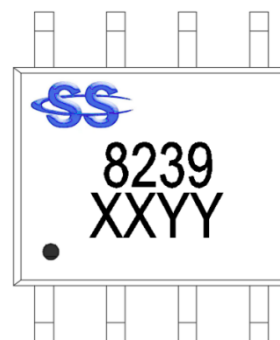
**100% UIS Tested.**

### ➤ Applications

- Load Switch
- NB battery
- DCDC conversion

### ➤ Ordering Information

Device	Package	Shipping
SSC8239GS1	SOP8	2500/Reel



(Y: year/W: week)

Marking

**➤ Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
$V_{DSS}$	Drain-to-Source Voltage	-35	V	
$V_{GSS}$	Gate-to-Source Voltage	$\pm 20$	V	
$I_D$	Continuous Drain Current <sup>d</sup>	TC=25 $^{\circ}\text{C}$	-68	A
		TC=100 $^{\circ}\text{C}$	-37	
$I_{DSM}$	Continuous Drain Current <sup>a</sup>	TA=25 $^{\circ}\text{C}$	-16	A
		TA=70 $^{\circ}\text{C}$	-11	
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	-272	A	
$I_{AS}$	Avalanche Current <sup>b</sup> L=0.5mH	-34	A	
$E_{AS}$	Avalanche Energy <sup>b</sup> L=0.5mH	289	mJ	
$P_D$	Power Dissipation <sup>d</sup>	TC=25 $^{\circ}\text{C}$	44	W
		TC=100 $^{\circ}\text{C}$	17	W
$P_{DSM}$	Power Dissipation <sup>a</sup>	TA=25 $^{\circ}\text{C}$	2.5	W
		TA=70 $^{\circ}\text{C}$	1.6	W
$T_J$	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$	
$T_{STG}$	Storage temperature range	-55 to 150		

**➤ Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>	50	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance <sup>c</sup>	22	
	Junction-to-Case Thermal Resistance <sup>d</sup>	2.8	

Note:

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper,in a still air environment with  $T_A=25^{\circ}\text{C}$ .The value in any given application depends on the user is specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_D$  is based on  $T_J(\text{MAX})=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The value of  $R_{\theta JC}$  has been determined of the temperature difference between junction and the case surface in contact with water cooled copper heat sink .

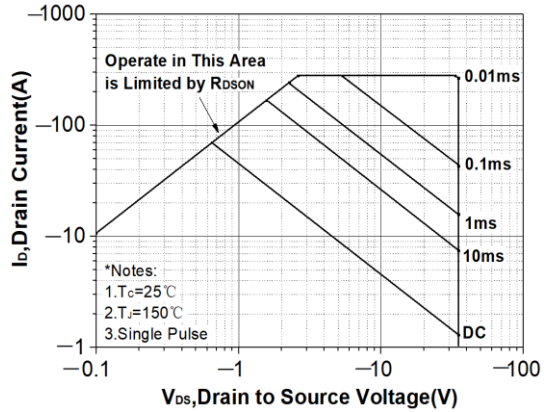
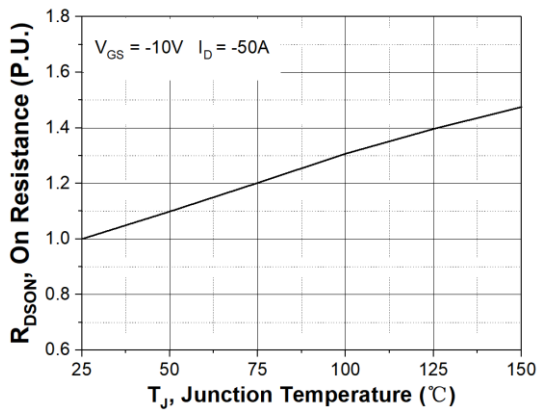
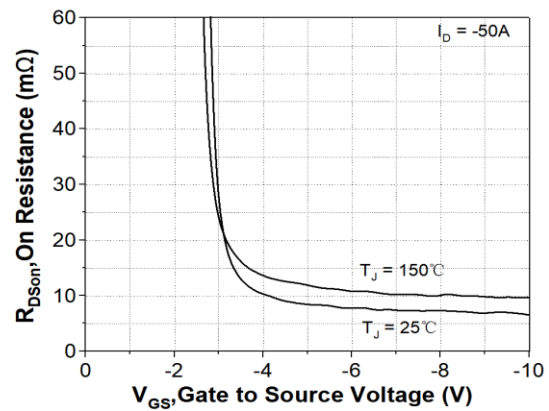
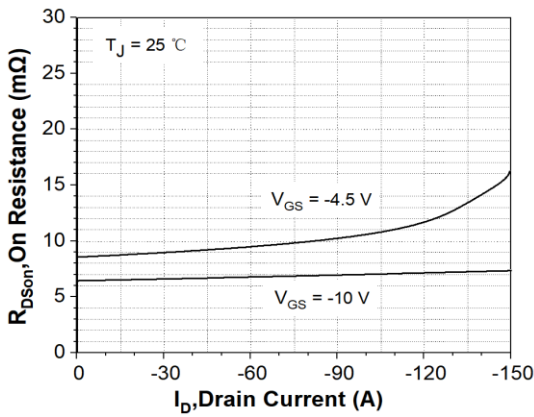
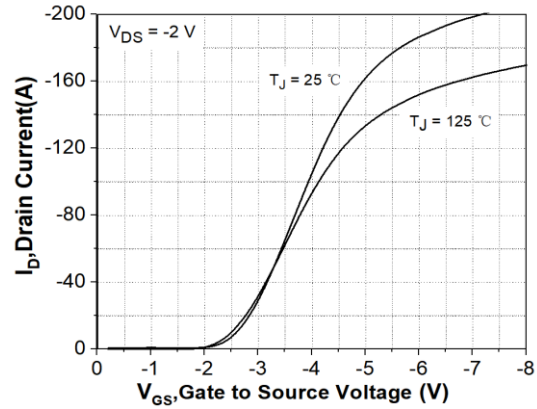
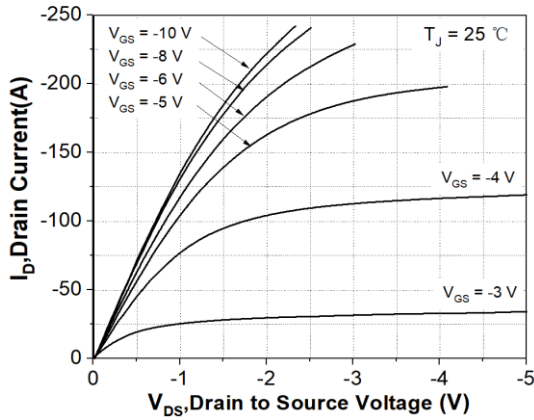


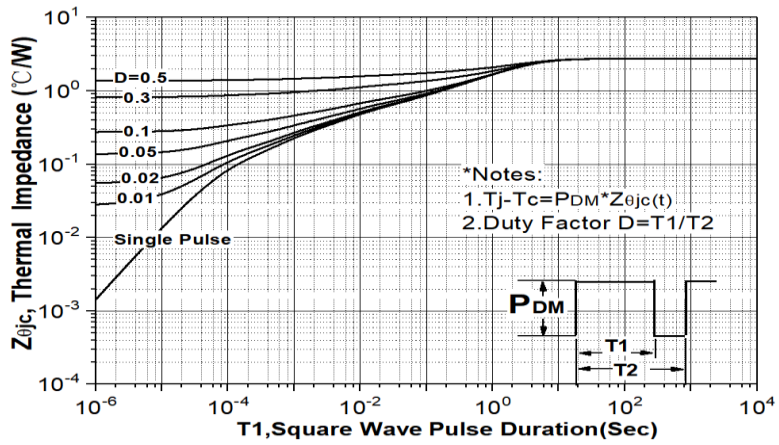
➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-35			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.4	-3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-15A$		6	7.5	mR
		$V_{GS}=-4.5V, I_D=-10A$		8	10	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$G_{FS}$	Transconductance	$V_{DS}=-5V, I_D=-10A$		11		S
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=-10A$		-0.8	-1.3	V
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		4800		pF
$C_{oss}$	Output Capacitance			510		
$C_{rss}$	Reverse Transfer Capacitance			410		
$Q_G$	Total Gate charge	$V_{GS}=-10V, V_{DS}=-15V, I_D=-20A$		80		nC
$Q_{GS}$	Gate to Source charge			10		
$Q_{GD}$	Gate to Drain charge			19		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=-10V, V_{DS}=-15V, R_L=0.75R, R_G=3R$		17		ns
$T_r$	Rise time			50		
$T_{D(OFF)}$	Turn-off delay time			110		
$T_f$	Fall time			25		
$T_{rr}$	Diode Recovery Time	$I_F=-20A, di/dt=500A/\mu s$		25		ns
$Q_{rr}$	Diode Recovery Charge			17		nC

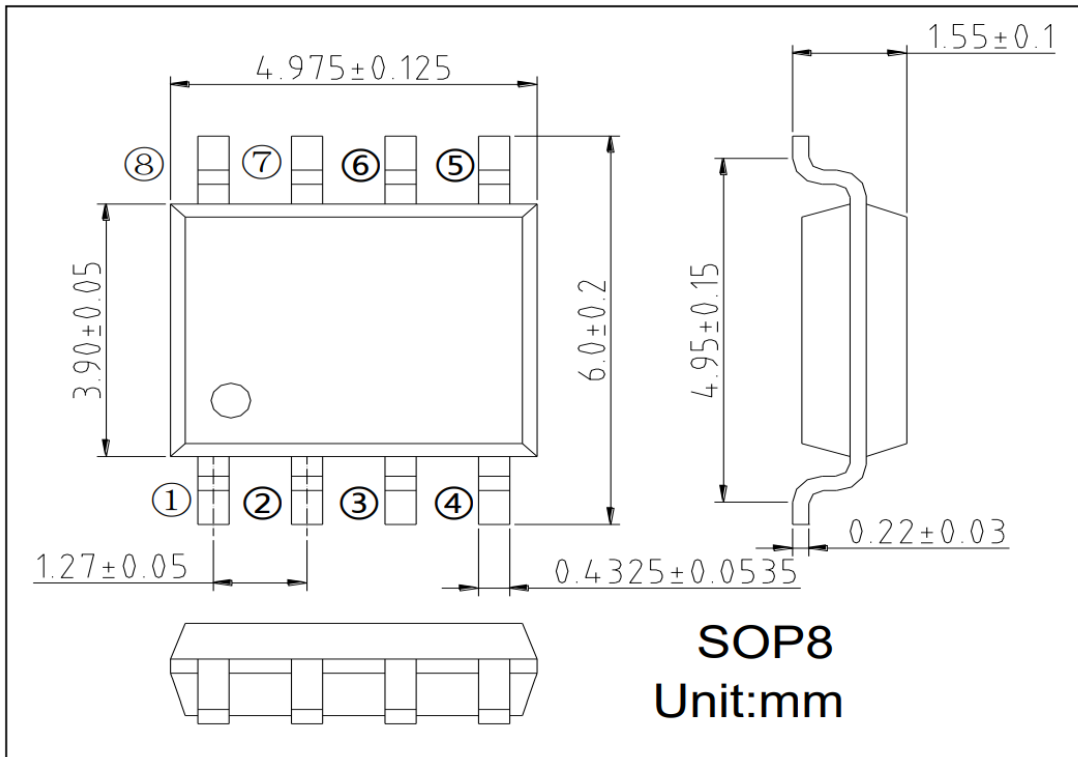


➤ Typical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)





➤ Package Information





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